

1. (Previously amended): A semiconductor device, comprising:
 - a trench formed in a substrate;
 - a diffusion region surrounding the trench to form a buried plate;
 - a first conductive material formed in the trench, wherein the first conductive material comprises a pillar extending from a bottom of the trench, wherein the first conductive material contacts the buried plate along an entire bottom portion of the trench and along a lower portion of the sidewalls of the trench, and wherein the first conductive material and the buried plate form a first electrode;
 - a second conductive material disposed in the trench to form a second electrode; and
 - a node dielectric layer formed between the first electrode and the second electrode.
2. (Original): The semiconductor device as recited in claim 1, wherein the first conductive material is formed into a plurality of pillars extending from the bottom of the trench.
3. (Original): The semiconductor device as recited in claim 2, wherein the plurality of pillars includes the second conductive material disposed between the plurality of pillars.
4. (Original): The semiconductor device as recited in claim 1, wherein the first conductive material includes one of a doped polysilicon and a doped amorphous silicon.
5. (Original): The semiconductor device as recited in claim 1, wherein the second conductive material includes doped amorphous silicon.

6. (Original): The semiconductor device as recited in claim 1, wherein the second conductive material is disposed between the first conductive material and the buried plate.

7-17. (Canceled).

18. (Previously added): A semiconductor device, comprising:

a trench formed in a substrate;

a diffusion region surrounding the trench to form a buried plate;

a first conductive material formed in the trench, wherein the first conductive material comprises a pillar extending from a bottom of the trench, wherein the first conductive material contacts the buried plate, and wherein the first conductive material and the buried plate form a first electrode;

a second conductive material disposed in the trench to form a second electrode; and

a node dielectric layer formed between the first electrode and the second electrode.

19. (Currently amended): The semiconductor device as recited in claim ~~7~~18, wherein the first conductive material is formed into a plurality of pillars extending from the bottom of the trench.

20. (Currently amended): The semiconductor device as recited in claim ~~8~~ 19, wherein the plurality of pillars includes the second conductive material disposed between the plurality of

pillars.

21. (Currently amended): The semiconductor device as recited in claim 7 18, wherein the first conductive material includes one of a doped polysilicon and a doped amorphous silicon.

22. (Currently amended): The semiconductor device as recited in claim 7 18, wherein the second conductive material includes doped amorphous silicon.

23. (Currently amended): The semiconductor device as recited in claim 7 18, wherein the second conductive material is disposed between the first conductive material and the buried plate.